NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02580D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

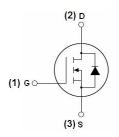
- V_{DS} =250V, I_{D} =80A $R_{DS(ON)}$ <18.5mΩ @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-263-2L top view

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|-----------|
| NCEP02580D | NCEP02580D | TO-263-2L | Ø330mm | 21mm | 800 units |

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|------------------------|------------|--------------|
| Drain-Source Voltage | V _{DS} | 250 | V |
| Gate-Source Voltage | V _G s | ±20 | V |
| Drain Current-Continuous | I _D | 80 | А |
| Drain Current-Continuous(T _C =100 °C) | I _D (100°C) | 56.6 | А |
| Pulsed Drain Current | I _{DM} | 320 | А |
| Maximum Power Dissipation | P _D | 300 | W |
| Derating factor | | 2 | W/℃ |
| Single pulse avalanche energy (Note 1) | E _{AS} | 1200 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 175 | $^{\circ}$ C |

NCEP02580D

Thermal Characteristic

| Thermal Resistance, Junction-to-Case Rejc 0.5 *C/W |
|--|
|--|

Electrical Characteristics (T_C=25°C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250µA | 250 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =250V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS},I_{D}=250\mu A$ | 2.5 | 3.5 | 4.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =40A | - | 16 | 18.5 | mΩ |
| Forward Transconductance | g FS | V _{DS} =10V,I _D =40A | 70 | - | - | S |
| Dynamic Characteristics | | | ' | ' | | ' |
| Input Capacitance | C _{lss} | \\ 405\\\\ 0\\ | - | 5400 | - | PF |
| Output Capacitance | Coss | $V_{DS}=125V, V_{GS}=0V,$ | - | 329 | - | PF |
| Reverse Transfer Capacitance | Crss | F=1.0MHz | - | 12 | - | PF |
| Switching Characteristics (Note 2) | | | ' | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 18 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =125 V , I_{D} =40 A | - | 26 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10 V , R_{G} =4.7 Ω | - | 41 | - | nS |
| Turn-Off Fall Time | t _f | | - | 11 | - | nS |
| Total Gate Charge | Qg |)/ 405\/\ 40A | - | 76.7 | | nC |
| Gate-Source Charge | Q _{gs} | V _{DS} =125V,I _D =40A, | - | 22.7 | | nC |
| Gate-Drain Charge | Q_{gd} | V _{GS} =10V | - | 20 | | nC |
| Drain-Source Diode Characteristics | | | • | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V,I _S =80A | - | | 1.2 | V |
| Diode Forward Current | Is | | - | - | 80 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = 40A | - | 140 | | nS |
| Reverse Recovery Charge | Qrr | di/dt = 100A/µs | - | 600 | | nC |

Notes:

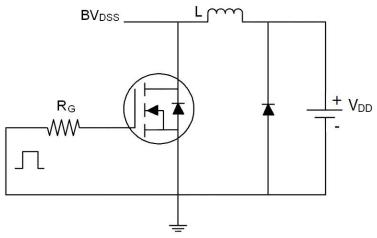
^{1.} EAS condition : Tj=25 $^{\circ}$ C,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25 Ω .

^{2.} Guaranteed by design, not subject to production

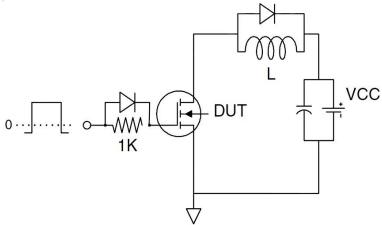
^{3.} These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Test Circuit

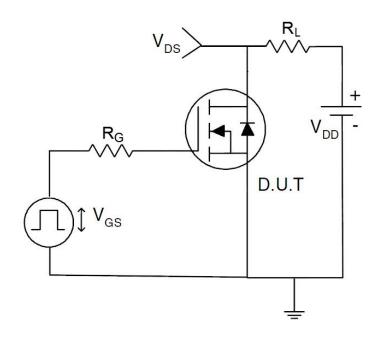
1) E_{AS} test Circuit

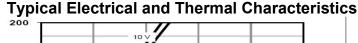


2) Gate charge test Circuit



3) Switch Time Test Circuit





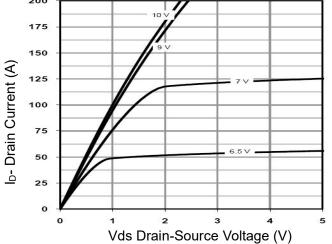


Figure 1 Output Characteristics

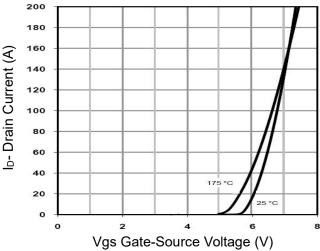


Figure 2 Transfer Characteristics

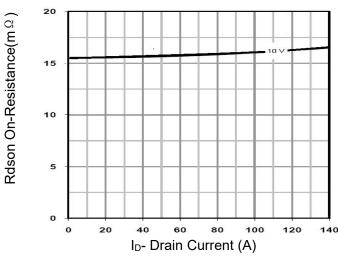


Figure 3 Rdson- Drain Current

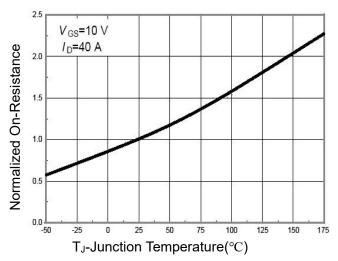


Figure 4 Rdson-JunctionTemperature

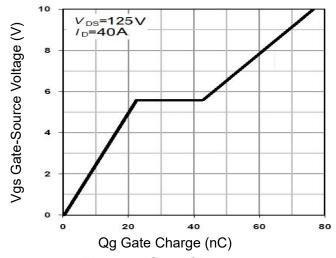


Figure 5 Gate Charge

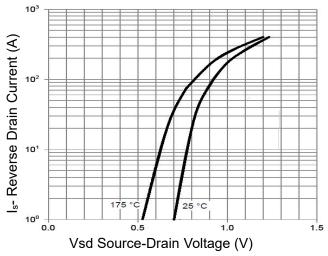
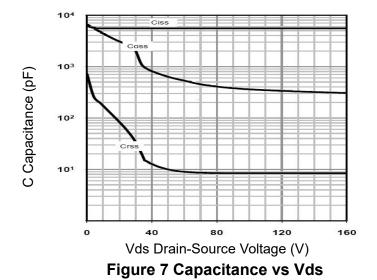


Figure 6 Source- Drain Diode Forward





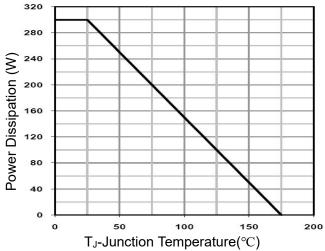
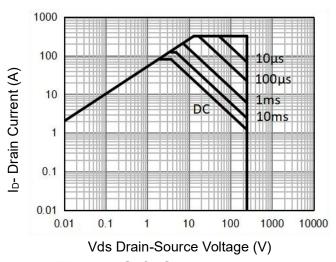


Figure 9 Power De-rating



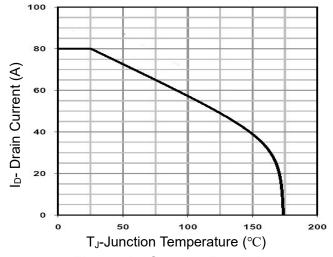
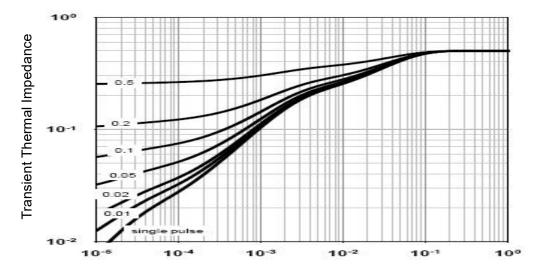


Figure 8 Safe Operation Area(Note 3)

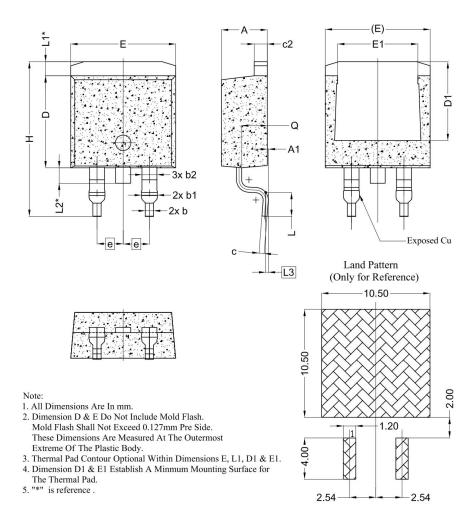
Figure 10 Current De-rating



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



| SYMBOL | DIMENSIONS | | | | |
|----------|------------------------------|-------|-------|--|--|
| STIVIBUL | MIN. | NOM. | MAX. | | |
| А | 4.24 | 4.44 | 4.64 | | |
| A1 | 0.00 | 0.10 | 0.25 | | |
| b | 0.70 | 0.80 | 0.90 | | |
| b1 | 1.20 | 1.55 | 1.75 | | |
| b2 | 1.20 | 1.45 | 1.70 | | |
| С | 0.40 | 0.50 | 0.60 | | |
| c2 | 1.15 | 1.27 | 1.40 | | |
| D | 8.82 | 8.92 | 9.02 | | |
| D1 | 6.86 | 7.65 | - | | |
| E | 9.96 | 10.16 | 10.36 | | |
| E1 | 6.89 | 7.77 | 7.89 | | |
| е | 2.54 BSC | | | | |
| н | 14.61 | 15.00 | 15.88 | | |
| L | L 1.78 2.3 | | 2.79 | | |
| L1 | 1.36 REF. | | | | |
| L2 | 1.50 REF. | | | | |
| L3 | L3 0.25 BSC Q 2.30 2.48 2.70 | | | | |
| Q | | | | | |

NCEP02580D

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